ON Semiconductor

Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,



FFB2227A / FMB2227A NPN & PNP General-Purpose Amplifier

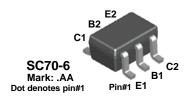
Description

This complementary device is a medium-power amplifier and switch, requiring collector currents up to 500 mA. Sourced from Process 19 and 63. See FFB2222A (NPN) and FFB2907A (PNP) for characteristics.

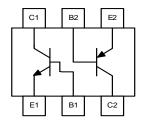
Ordering Information

Part Number	Top Mark	Package	Packing Method
FFB2227A	AA	SC70 6L	Tape and Reel
FMB2227A	001	SSOT 6L	Tape and Reel

Block Diagram

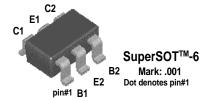


FFB2227A Device Package

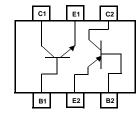


FFR2227∆	Internal C	onnoction

TRANSISTOR TYPE
C1 B1 E1 NPN
C2 B2 E2 PNP



FMB2227A Device Package



FMB2227A Internal Connection

Figure 1. Block Diagram

Absolute Maximum Ratings(1)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	500	mA
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	- 55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or lowduty cycle operations.
- 3. All voltages (V) and currents (A) are negative polarity for PNP transistors.
- 4. These Ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics(2)

Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Maxi	Units	
		FFB2227A	FMB2227A	Omis
P _D	Total Device Dissipation	300	700	mV
	Derate Above 25°C	2.4	5.6	mV/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	°C/W

Note:

2. PCB board size: FR-4 76 x 114 x 0.6T mm³(3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics(3)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
OFF CHAF	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage ⁽⁴⁾	I _C = 10 mA, I _B = 0	30			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA, I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 50 V, I _E = 0			30	nA
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 3.0 V, I _C = 0			30	nA
ON CHAR	ACTERISTICS					
	DC Current Gain	I _C = 1.0 mA, V _{CE} = 10 V	50			
h		I _C = 10 mA, V _{CE} = 10 V	75			
h _{FE}		I _C = 150 mA, V _{CE} = 10 V ⁽⁴⁾	100			
		I_C = 300 mA, V_{CE} = 10 $V^{(4)}$	30			
\/ (aat)	Collector-Emitter Saturation Voltage ⁽⁴⁾	I _C = 150 mA, I _B = 15 mA			0.4	V
V _{CE} (sat)		I _C = 300 mA, I _B = 30 mA			1.4	V
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽⁴⁾	I _C = 150 mA, I _B = 15 mA			1.3	V
SMALL SIG	SNAL CHARACTERISTICS					
f _T	Current Gain - Bandwidth Product	I _C = 50 mA, V _{CE} = 20 V, f = 100 MHz		250		MHz
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 100 kHz		4.0		pF
C _{ibo}	Input Capacitance	$V_{EB} = 2.0 \text{ V}, I_C = 0, f = 100 \text{ kHz}$		12		pF
NF	Noise Figure	I_C = 100 μA, V_{CE} = 10 V, R_S = 1.0 kΩ, f = 1.0 kHz		2.0		dB
SWITCHIN	G CHARACTERISTICS			•		
t _{on}	Turn-on Time			30		ns
t _d	Delay Time	$V_{CC} = 30 \text{ V, } I_{C} = 150 \text{ mA,}$ $I_{B1} = 15 \text{ mA}$		8.0		ns
t _r	Rise Time			20		ns
t _{off}	Turn-off Time	$V_{CC} = 6.0 \text{ V}, I_{C} = 150 \text{ mA},$ $I_{B1} = I_{B2} = 15 \text{ mA}$		80		ns
t _s	Storage Time			60		ns
t _f	Fall Time	ום: ושל ישוי או		20		ns

- 3. All voltages (V) and currents (A) are negative polarity for PNP transistors.
- 4. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2.0%.

Physical Dimensions

SC70 6L

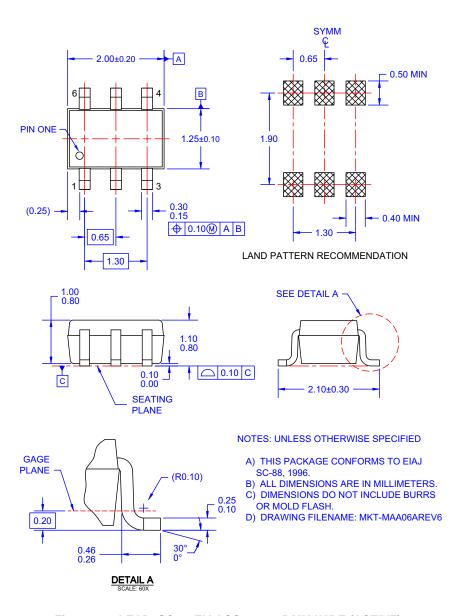


Figure 2. 6-LEAD, SC70, EIAJ SC-88, 1.25 MM WIDE (ACTIVE)

Package drawings are provided as a service to customers considering ON Semiconductor components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a ON Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of ON Semiconductor's worldwide terms and conditions, specifically the warranty therein, which covers ON Semiconductor products.

Physical Dimensions (Continued)

SSOT 6L

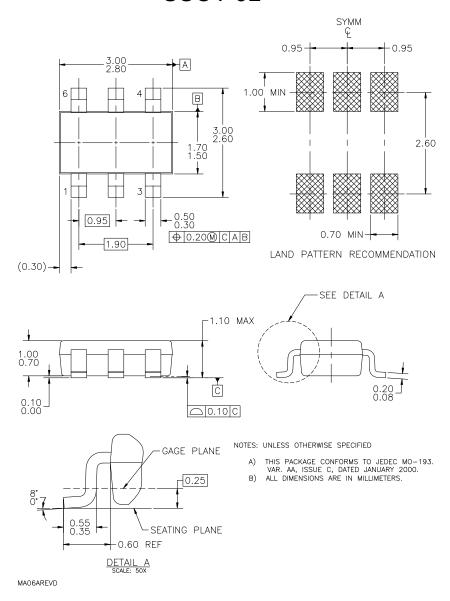


Figure 3. 6-LEAD, SUPER SOT-6, JEDEC MO-193, 1.6 MM WIDE (ACTIVE)

Package drawings are provided as a service to customers considering ON Semiconductor components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a ON Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of ON Semiconductor's worldwide terms and conditions, specifically the warranty therein, which covers ON Semiconductor products.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor nessure any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, a

Phone: 81-3-5817-1050

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

♦ © Semiconductor Components Industries, LLC

www.onsemi.com